



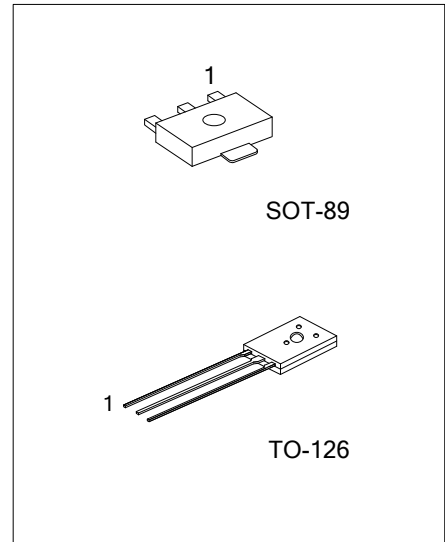
2SB824

PNP SILICON TRANSISTOR

PNP PLANAR SILICON TRANSISTOR

FEATURES

* Low collector-to-emitter saturation voltage:
 $V_{CE(SAT)} = -0.4V \text{ max} / I_C = -3A, I_B = -0.3A$



Lead-free: 2SB772SL
 Halogen-free: 2SB772SG

ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SB824L-x-AB3-R	2SB824G-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SB824L-x-T60-K	2SB824G-x-T60-K	TO-126	B	C	E	Bulk

<p>2SB824L-x-AB3-R</p>	<p>(1) K: Bulk, R: Tape Reel (2) T60: TO-126, AB3: SOT-89 (3) x: refer to Classification of h_{FE1} (4) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector to Base Voltage		V_{CBO}	-60	V
Collector to Emitter Voltage		V_{CEO}	-50	V
Emitter to Base Voltage		V_{EBO}	-6	V
Collector Current		I_C	-5	A
Collector Current (Pulse)		I_{CP}	-9	A
Collector Dissipation	SOT-89	P_C	500	mW
	TO-126		1	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

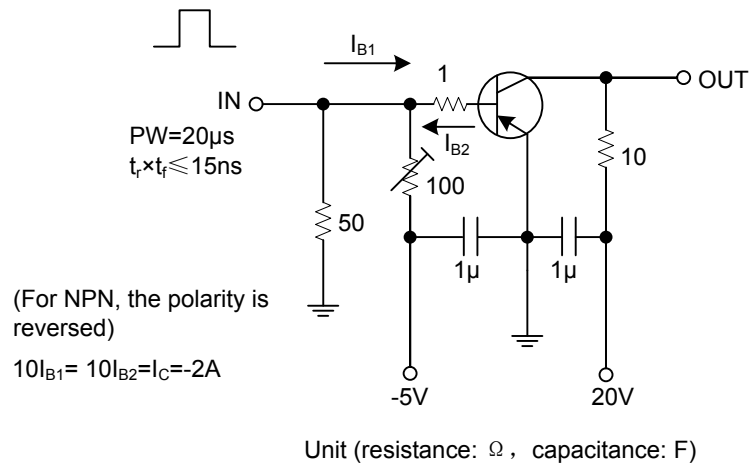
■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-to-Base Breakdown Voltage	BV_{CBO}	$I_C = -1mA, I_E = 0$	-60			V
Collector-to-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA, R_{BE} = \infty$	-50			V
Emitter-to-Base Breakdown Voltage	BV_{EBO}	$I_C = 0, I_E = -1mA$	-6			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	mA
DC Current Gain	h_{FE1}	$V_{CE} = -2V, I_C = -1A$	70		360	
	h_{FE2}	$V_{CE} = -2V, I_C = -3A$	30			
Gain Bandwidth Product	f_T	$V_{CE} = -5V, I_C = -1A$		30		MHZ
Output Capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$		100		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -3A, I_B = -0.3A$			-0.4	V
Turn-ON Time	t_{ON}	See specified test circuit		0.1		µs
Storage Time	t_{STG}	See specified test circuit		1.4		µs
Fall Time	t_F	See specified test circuit		0.2		µs

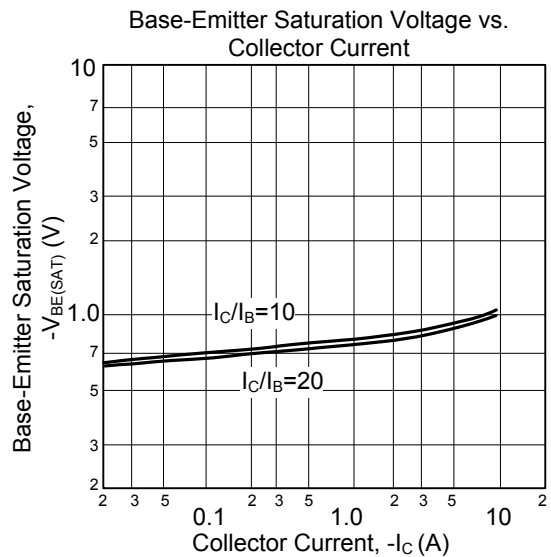
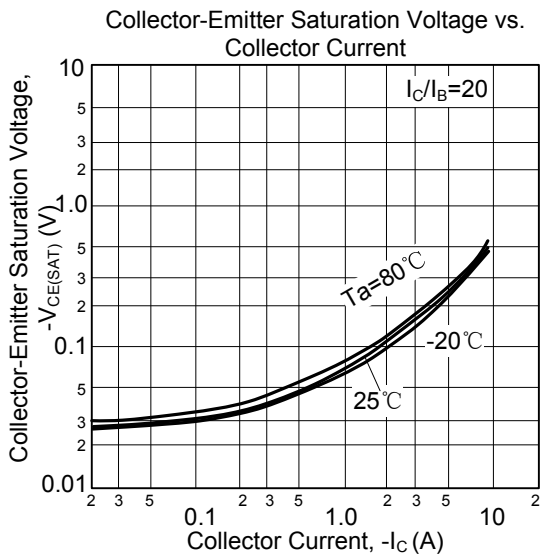
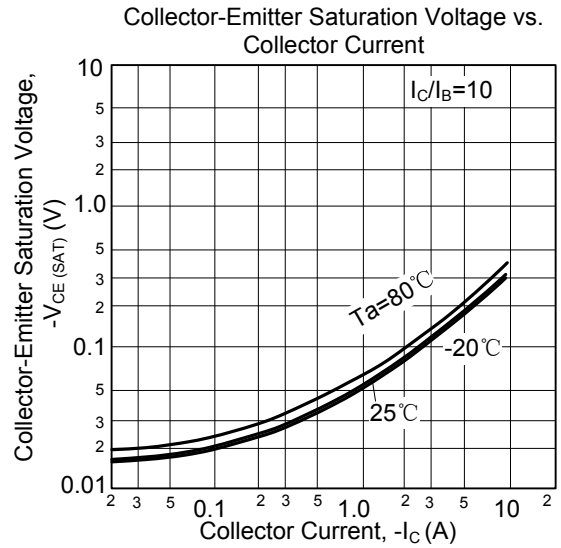
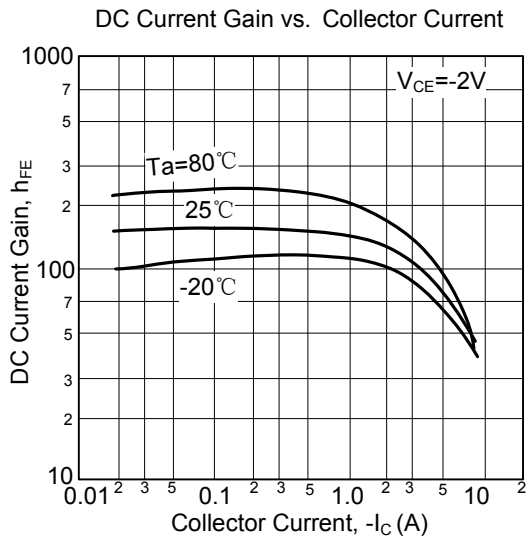
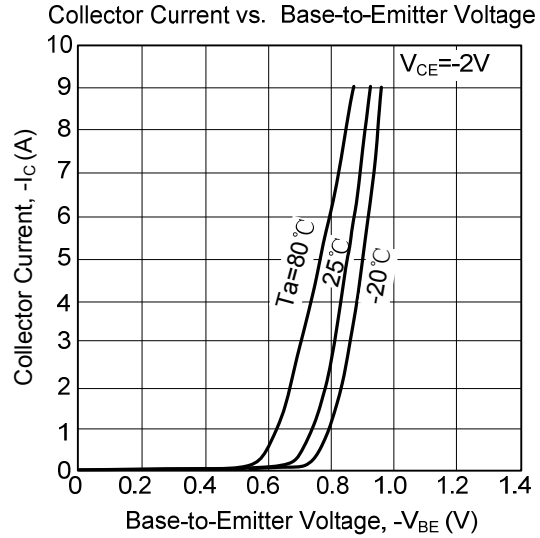
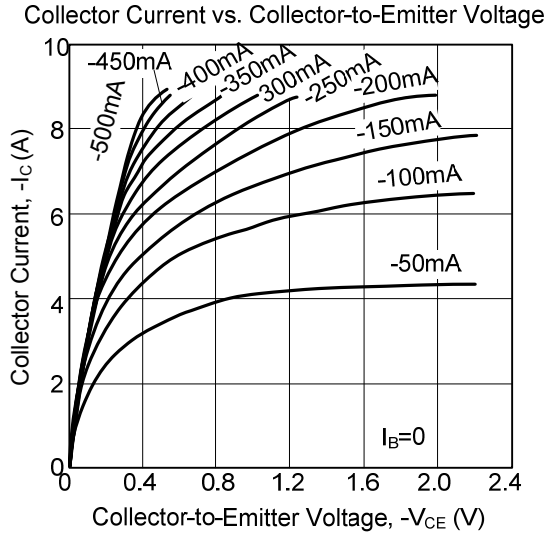
■ CLASSIFICATION of h_{FE1}

RANK	Q	R	S
RANGE	70-140	100-200	180-360

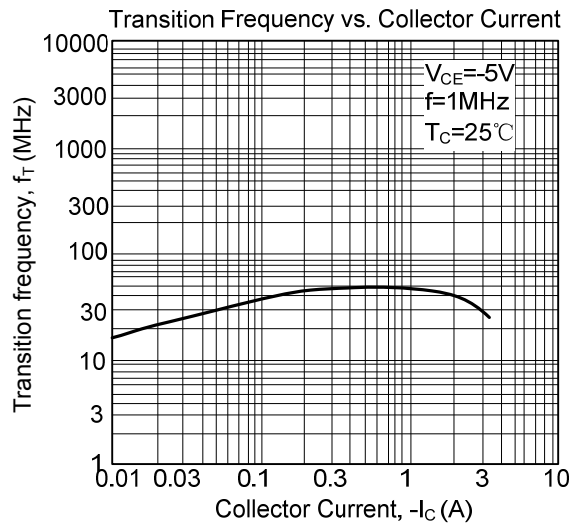
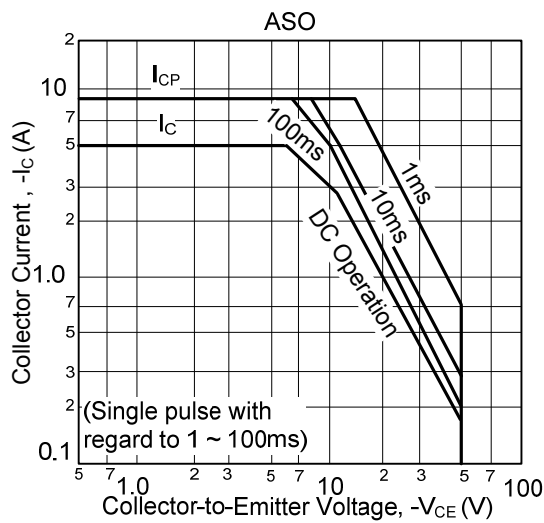
SWITCHING TIME TEST CIRCUIT



TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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